

Microwave dielectric characteristics of Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics

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Abstract

The sintering characteristics, phase composition, and microwave dielectric properties of Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1300–1500 °C have been investigated. Results show that Nb⁵⁺ and Al³⁺ can co-substitute for Ti⁴⁺ and form Ti_{0.8}Al_{0.1}Nb_{0.1}O₂, which can lower effectively the sintering temperature, and improve the quality factor of 0.9Al₂O₃–0.1TiO₂ ceramics.

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1. Introduction

Dielectric materials for microwave applications have been used in mobile phones, wireless local area networks (LAN), and intelligent transport systems (ITS). Recently, they are planned to be applied in ultrahigh speed wireless LAN in millimeter-wave, because they can reduce the resource of electromagnetic wave. Dielectric ceramics for millimeterwave applications are also planned for use in ITS, including a car anti-collision system [1].

In order to meet this application, high performance microwave dielectric materials with a high quality factor (Q), and a low dielectric constant (ϵ_r) are required. Moreover, near-zero temperature coefficient of resonant frequency (τ_f) is also needed to provide stability at various service temperatures. Q value is generally evaluated as $Q \cdot f$ (f is resonant frequency) because $Q \cdot f$ is almost independent on resonant frequency [2].

Alumina (Al₂O₃) is used as a ceramic substrate material because of its high thermal conductivity, suitable dielectric constant, and low dielectric loss. However, it has a large negative τ_f value (–60 ppm/°C) [3,4]. In order to shift the τ_f value of Al₂O₃ ceramics, TiO₂ with positive τ_f value (+450 ppm/°C) [5] can be introduced to form a composition

of Al₂O₃–TiO₂. It shows that the τ_f value of the 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1550 °C can reach +1.5 ppm/°C. To lower the sintering temperature of the 0.9Al₂O₃–0.1TiO₂ composition, suitable oxides, low-melting-point glasses, and smaller particle size of the starting materials should be used. In this study, the effects of Nb₂O₅ content on microwave dielectric properties of the 0.9Al₂O₃–0.1TiO₂ ceramics are reported. Relationships among the sintering temperature, phase compositions, and microwave dielectric properties of the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics are also discussed.

2. Experimental procedures

Al₂O₃ and TiO₂ with purity higher than 99.5% were used as starting materials, and mixed according to the composition of 0.9Al₂O₃–0.1TiO₂ by ball-milling for 3 h in deionized water. After drying and grinding, the powder was calcined at 1100 °C for 3 h. The calcined 0.9Al₂O₃–0.1TiO₂ powder was mixed with Nb₂O₅ by ball-milling in deionized water for 1 h. After drying and mixing with polyvinylalcohol as binder, the mixed powder was pressed into pellets in a steel die. After debinding, these pellets were sintered at 1300–1500 °C for 3 h.

The crystal phases of the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics were analyzed by X-ray powder diffraction (XRD) using Cu K α radiation and electron-probe microanalysis (EPMA). The ϵ_r and $Q \cdot f$ value were measured in the TE₀₁₁ mode by the Hakki and Coleman's dielectric resonator method which was improved by Courtney [6,7], using an Advantest

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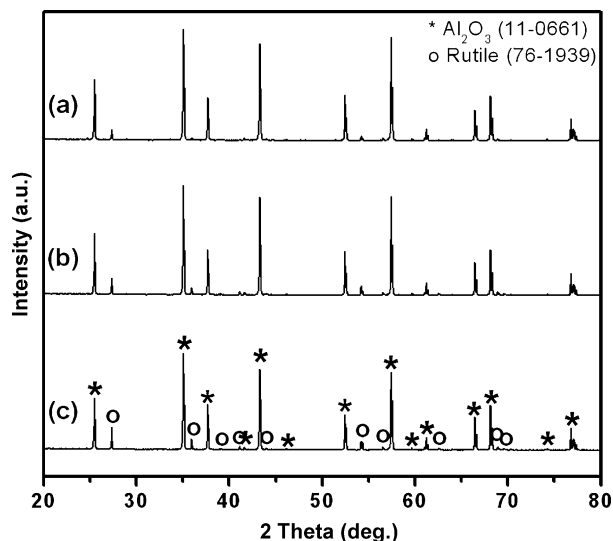


Fig. 1. X-ray diffraction patterns of the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1400 °C: (a) 0.3 wt.%; (b) 0.5 wt.%; and (c) 0.8 wt.%.

Table 1

Element content in the white area in the 0.9Al₂O₃–0.1TiO₂ ceramics with 0.5 wt.% Nb₂O₅ sintered at 1400 °C.

Element	Al	Ti	Nb	O
Content (at.%)	2.82	27.42	3.06	66.71

R3767C network analyzer. The τ_f value was defined by formula:

$$\tau_f = \frac{1}{f(20)} \times \frac{f(80) - f(20)}{80 - 20} \quad (1)$$

where $f(20)$ and $f(80)$ are the resonant frequency at 20 and 80 °C, respectively.

3. Results and discussion

Fig. 1 shows XRD patterns of the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1400 °C for 3 h. Al₂O₃ and TiO₂ are two main crystalline phases in the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ system. With the increase of Nb₂O₅, the X-ray diffraction intensity of Al₂O₃ phase decreases while the intensity of TiO₂ phase increases.

Fig. 2 shows backscattered electron image and mapping of the elements by EPMA for the 0.9Al₂O₃–0.1TiO₂ ceramics

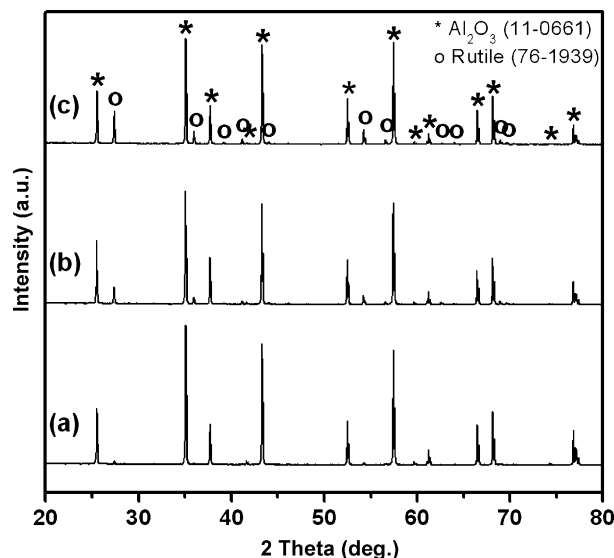


Fig. 3. X-ray diffraction patterns of the 0.5 wt.% Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1300–1500 °C, respectively. (a) 1300 °C; (b) 1400 °C; and (c) 1500 °C.

with 0.5 wt.% Nb₂O₅ sintered at 1400 °C. It can be observed clearly from the backscattered electron image that two phases exist in the system. The white area represents rutile phase while the gray area is Al₂O₃ phase, which agrees well with the above XRD results, as shown in Fig. 1.

Table 1 shows element content in the white area in the 0.9Al₂O₃–0.1TiO₂ ceramics with 0.5 wt.% Nb₂O₅ sintered at 1400 °C. A small amount of Al³⁺ and Nb⁵⁺ cations is included in the rutile phase, because the equal mole Al³⁺ and Nb⁵⁺ cations can co-substitute for Ti⁴⁺ cation and form Ti_{0.8}Al_{0.1}Nb_{0.1}O₂ solid solution. Therefore, with the increase of Nb₂O₅ content, the amount of Ti_{0.8}Al_{0.1}Nb_{0.1}O₂ solid solution phase increases while that of Al₂O₃ phase reduces in the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ system, which results into the enhancement in the X-ray diffraction intensities of rutile phase and the weakening in those of Al₂O₃ phase, as shown in Fig. 1.

Fig. 3 shows XRD patterns for the 0.5 wt.% Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1300–1500 °C for 3 h. With the increase of the sintering temperature, the X-ray diffraction intensities of Al₂O₃ phase reduce gradually while those of rutile phase enhance obviously, which indicates that the increase in sintering temperature can promote the formation of Ti_{0.8}Al_{0.1}Nb_{0.1}O₂ solid solution.

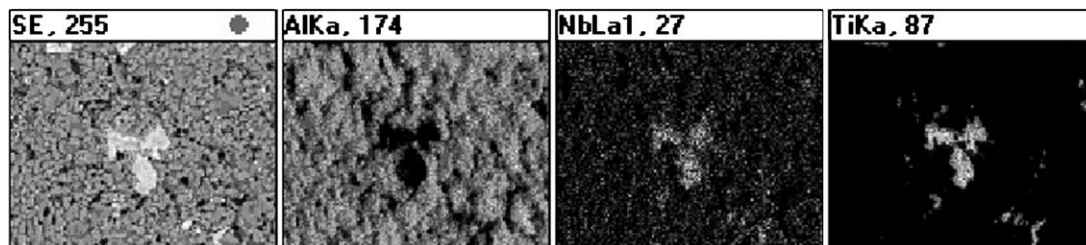


Fig. 2. Backscattered electron image and mapping of the elements by EPMA for the 0.9Al₂O₃–0.1TiO₂ ceramics with 0.5 wt.% Nb₂O₅ sintered at 1400 °C.

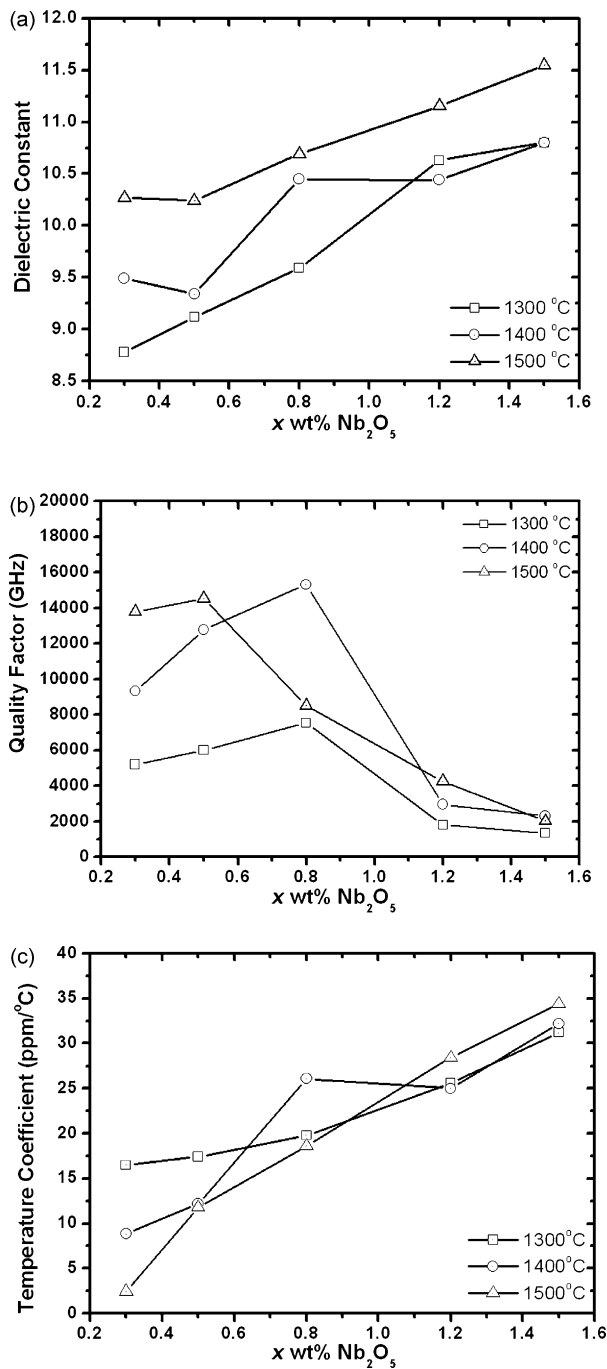


Fig. 4. Microwave dielectric properties of the 0.9Al₂O₃–0.1TiO₂ ceramics as a function of sintering temperature and Nb₂O₅ content.

Microwave dielectric properties of the 0.9Al₂O₃–0.1TiO₂ ceramics as a function of sintering temperature and Nb₂O₅ content are shown in Fig. 4. With the increase of Nb₂O₅ content or sintering temperature, the ϵ_r value takes on an increasing tendency, and the $Q \cdot f$ value increases initially and then reduces. Furthermore, the τ_f value increases gradually with Nb₂O₅ content while it is nearly independent on sintering temperature.

An increase in Nb₂O₅ content or sintering temperature can result in an increase in the amount of Ti_{0.8}Al_{0.1}Nb_{0.1}O₂ solid solution in the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ system, as

shown in Figs. 1 and 3 respectively. According to Shannon [8], the polarizability of Nb⁵⁺ cation is 3.98 Å, which is bigger than that of Ti⁴⁺ ($\alpha = 2.94$ Å). As a result, the ϵ_r value increases with the augment of Nb₂O₅ content and sintering temperature (see Fig. 4(a)).

The $Q \cdot f$ value is generally affected not only by the lattice vibrational modes, but also by the density, the second phases, the impurity, the lattice defect, crystallizability, and inner stress. The increase in sintering temperature is beneficial to the densification and crystallizability until the $Q \cdot f$ value reaches the maximum. The further increase in sintering temperature will result in the appearance of abnormal grains and pores and consequently lead to the reduction of the $Q \cdot f$ values [9]. It can be observed from Fig. 4(b) that the $Q \cdot f$ value can reach the maximum 15,320 GHz when the sintering temperature is equal to 1400 °C, lower than the densification temperature of the 0.9Al₂O₃–0.1TiO₂ ceramics by about 150 °C, which indicates that Nb₂O₅ addition can enhance the sinterability of the 0.9Al₂O₃–0.1TiO₂ system. Therefore, the increase in Nb₂O₅ content can improve the density and crystallizability, which results in the increase of the $Q \cdot f$ value. However, at the same time, the amount of the impurity and defect increases with Nb₂O₅ content, which deteriorates the $Q \cdot f$ value. Therefore, as the $Q \cdot f$ value increases initially and then reduces with the increase of Nb₂O₅ content.

Nb₂O₅ addition can heighten the τ_f value of the 0.9Al₂O₃–0.1TiO₂ ceramics, as shown in Fig. 4(c). When x is equal to 0.3, the τ_f can be controlled to near zero value. It is not obvious that the effect of sintering temperature on the τ_f value. To understand clearly the relationship among Nb₂O₅ content, sintering temperature and τ_f value, further investigation must be performed.

Compared with 0.9Al₂O₃–0.1TiO₂ ceramics sintered at 1550 °C with an ϵ_r value of 11.8, a $Q \cdot f$ value of 8000 GHz and a τ_f value of +1.5 ppm/°C, the Nb₂O₅-added 0.9Al₂O₃–0.1TiO₂ ceramics have more excellent sinterability and $Q \cdot f$ value.

4. Conclusion

Nb₂O₅ addition can lower effectively the sintering temperature of the 0.9Al₂O₃–0.1TiO₂ ceramics. The equal mole Nb⁵⁺ and Al³⁺ can co-substitute for Ti⁴⁺ and form Ti_{0.8}Al_{0.1}Nb_{0.1}O₂ solid solution. With the increase of Nb₂O₅ content or sintering temperature, the ϵ_r value takes on an increasing tendency, and the $Q \cdot f$ value increases initially and then reduces. Furthermore, the τ_f value increases gradually with Nb₂O₅ content while it is nearly independent on sintering temperature.

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